



N-Channel Enhancement Mode Field Effect Transistor

Product Summary

- V_{DS} 80V
- I_D 100A
- $R_{DS(ON)}$ P-MOSFET 11/Lang (en-US) BDC q0.00000 841.01W h0 0 1.517t0 G[A] TJTJETQq0.00000888 0 595

Maximum Drain-Source Continuous Current	I _S		-	-3	100	A
Gate resistance	R _G	f=1MHz	-	2	-	Ω

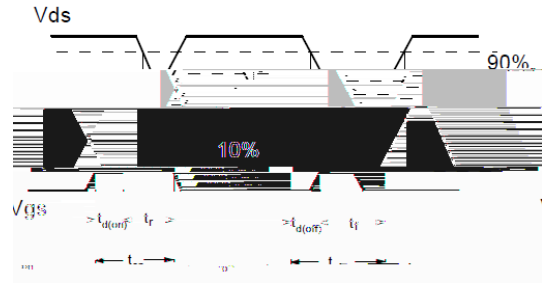
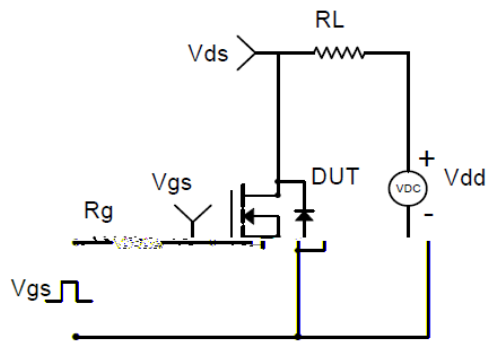
Transconductance(181.75 637.39 0.48 0.48 r



YJG100G08E

Typical Performance Characteristic



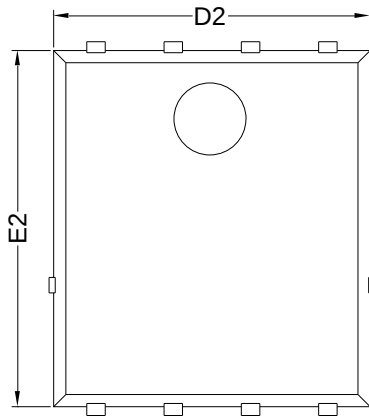


Resistive Switching Test Circuit &

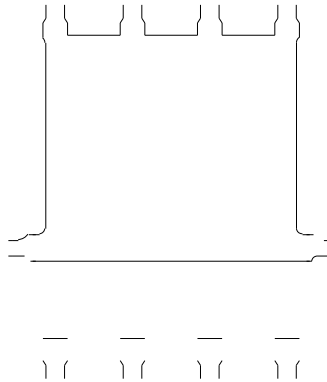


YJG100G08E

■ PDFN5060-8L-B-1.1MM Package information



Top View



Bottom View

Side View

SYMBOL	MILLIMETER		
	MIN	NOM	MAX
D	5.15	5.35	5.55
E	5.95	6.15	6.35
A	1.00	1.10	1.20
A1	0.254 BSC		
A2			0.10
D1	3.92	4.12	4.32
E1	3.52	3.72	3.92
D2	5.00	5.20	5.40
E2	5.66	5.86	6.06
E3	0.254 REF		
E4	0.21 REF		
L1	0.56	0.66	0.76
L2	0.50 BSC		
b	0.31	0.41	0.51
e	1.27 BSC		

Note:

- 1.Controlling dimension:in millimeters.
- 2.General tolerance:±0.10mm.
- 3.The pad layout is for reference purposes only.



Disclaimer

The information presented in this document is for reference only. Yangzhou Yangjie Electronic Technology Co., Ltd. reserves the right to make changes without notice for the specification of the products displayed herein to improve reliability, function or design or otherwise.

The product listed herein is designed to hs (n)30()42(t)-10(o)30()-1d(i)-14(a)(si)a i rod()-1ce i rp7(d)3(o)3(cu)30(m)-34(e)30()-10(o)30()-1